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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

oplication of: Li YAO, et al.

Application No.: 10/689,043

Art Unit:

Filed: October 21, 2003

Examiner:

For:

ABRASIVE-FREE CHEMICAL MECHANICAL

POLISHING COMPOSITION AND POLISHING

PROCESS CONTAINING SAME

Atty Docket No.: 060937-0151-US

(Former P&E No. 8317-0151-999)

Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

SUBMISSION OF REVOCATION OF ORIGINAL POWER OF ATTORNEY AND GRANT OF NEW POWER OF ATTORNEY

Enclosed is a copy of the Revocation of Original Power of Attorney and Grant of New Power of Attorney by the Assignee, EKC Technology, Inc. Assignee directs the Patent and Trademark Office to send all future correspondence to:

CUSTOMER NO. 009629 MORGAN, LEWIS & BOCKIUS LLP

1111 Pennsylvania Avenue, N.W. Washington, D.C. 20004 Tel. 202-739-3000

If there is any fee due in connection with the filing of this Submission, please charge the fee to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

Respectfully submitted,

April 26, 2004

By:

Christopher G. Hayden Reg. No. 44,750 MORGAN, LEWIS & BOCKIUS LLP

1111 Pennsylvania Avenue, N.W.

Washington, D.C. 20004

Tel: 202-739-3000 Fax: 202-739-3001



REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Assignee:

EKC Technology, Inc.

Date: 29 March 2004

Signature:

Typed Name Michael A. Fury

Position/Title Vice President, R&D and Engineering

Address:

2520 Barrington Court, Hayward, California 94545

Schedule A					
App #	The state of the s	Joyentor(s)	Filing s se Date : 1	New Allomey Dockel No	Former Attorney
	Compositions for Cleaning Organic				
09/903,064	and Plasma Etched Residues for Semiconductor Devices	Small, et al.	07/10/2001	60027 004 110	0047 004 000
09/903,004	Method of and Apparatus for	Sitiali, et al.	07/10/2001	60937-091-US	8317-091-999
09/874,330	, and the second	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
	Chemical Mechanical Polishing				
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
	Oxalic Acid as a Semiaqueous				
10/421,706	Cleaning Product for Copper and Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/421,700	Sulfoxide Pyrolid(in)one Alkanolamine	Lee, et al.		00937-110-03	0317-110-999
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
	Method for the Deposition of Materials				
09/876,944		Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
10/007,134	Post Etch Cleaning Composition for Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
10/007,104	Photolytic Conversion Process to	raylle, et al.	12/04/2001	00937-123-03	0317-123-999
10/263,701	•	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
09/988,545	Potential	Lee, et al.	. 11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for Chemically Treating A Substrate				
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
10/000,100	Cleaning Solution Including	· aton ot an	0172072002	00307-123-00	0317-129-333
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
1	Process for the Use of Bis-Choline				
	and Tris-Choline in the Cleaning of Quartz-Coated Polysilicon and Other	·			.
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
10/000/001	Cleaning Compositions Containing	Onami, ot al.	10,22,2000	00007-100-00	0017-100-000
	Hydroxylamine Derivatives and				
	Process Using Same for Residue				
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
•	Composition for Eufoliation Asset to				·
10/689,616	Composition for Exfoliation Agent to be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
.0/000,010	Reducing Oxide Loss When Using	. Incinit IV Carrel	10/22/2003	00331-141-03	. 0317-141-535
	Fluoride Chemistries to Remove Post-	· · ·	1		
	Etch Residues in Semiconductor				
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver				
	and Silver Oxide Films and Patterned				
10/716,838	Films .	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
	Semiconductor Process Residue	l an akal	06/06/2002	60027 440 116	9247 440 000
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	System and Method for Cleaning Workpieces Using Supercritical		•		
60/460 936	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
60/469,826	Carbon bloxide	1 dry, ocui.			
	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing				
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
		•			·
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
	Hydrothermal Treatment of		40/00/0000	60607 467 116	0247 407 000
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US 60937-168-US	8317-167-999 8317-168-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-100-03	6317-100-999
40/404 405	— Chemical-Mechanical-Polishing — Composition and Process	Small, et al.	03/27/2003	60937-171-US	8317-171-999
10/401,405	Aqueous Phosphoric Acid	Sittali, et al.	03/2/12003	00357-171-05	0317-171-333
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	-10/21/2003	60937-172-US	8317-172-999
10/000,300	Load Lock System for Supercritical	Daviot, ot al.	10.21.200	00001 112 00	
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/100,000	Automated Dense Phase Fluid				· ·
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for				
	Electrohydrodynamic Cleaning of		•		·
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
	Titanium Carboxylate Films for Use in	•			
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing				
60/400 700	Fluoride for Use During	Lingagues of of	04/49/2002	60027 495 DD	8317-185-888
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	0317-100-000
	Cleaning Composition for Removing	· •.			
EDIAGA 125	Resists and Manufacturing Method of Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
60/464,125	Deposition of Permanent Polymer	miasawa, et ai.		00301-100-FIX	3311-100-000
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	.8317-187-999
10/422,212	Sauctures for OLED Fabrication	(Vollail, et al.	J-12012003	100001-101-00	00

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10//10 050	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,858	Cleaning Compositions and Method of	TT AT IVIGIT LCC	00/20/2000		
40/620 200	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
10/630,300	Compositions and Methods for	Training Loo	01100.2000		
	Rapidly Removing Overfilled		•		•
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
00/3/10,337	CMP Method for Copper, Tungsten,				
	Titanium, Polysilicon, and Other		•		
	Substrates Using Organosulfonic				
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
10,000,000	PeriodicAcid Compositions for			•	
	Polishing Nobel Metal/High K	•			
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
	Cerium Oxide Abrasives for Chemical				
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
·		•			
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing	0 (44/04/0000		8317-206-888
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	6317-200-666
	Periodic Acid Compositions for	Debort Condi	08/14/2003	60937-207-PR	8317-207-888
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	00/14/2003	00337-207-110	
10/000 700	Chemical-Mechanical-Polishing	Small, et al.	10/10/2003	60937-211-US	8317-211-999
10/683,730	Compositions and Process Alumia Abrasive for Chemical	Siliali, et al.	10/10/2003	00001-211-00	0017 211 000
00/544 000	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
60/514,020	. Wechanical Polishing	Primpperi. Oneic	10/2//1000	00001 210 111	
	Chemical Mechanical Polishing	•			
	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
00/302,931	Compositions for Chemical	Taximirating 50 and			·
İ	Mechanical Planarization of Tantalum	·	•		
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
10/000,417	Alumina Abrasive for Chemical				
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	Particulate or Particle-Bound				
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound .	•			.0047.047.000
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI	•			
	Features on Semiconductors: Water	_	40,000,0000	00007 000 00	0247-202-009
60/533,054	Polishing with Ceria Slurries	Yu, et al	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and	, ,			
	Copper Contamination From Low-K	•			
	Dielectrics Using Superciritcal CO2	Jarama Daviet	10/14/2002	60937-225-PR	8317-225-888
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	00931-223-FR	
10/004 000	Method and Apparatus for Substrate	Lee, et al.	10/29/2003	60937-226-US	8317-226-999
10/694,999	Pre-Treatment	Lee, et al.	10/20/2000	, 3000, 220 00	

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LAPP#	Ville 3	andnventor(s)	Filling Date	New Attorney Docket No.	Former Attorney Docket No.:
	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937 - 228-PR	8317-228-888